

GSM1072KJZF

20V N-Channel Enhancement Mode MOSFET

Product Description

GSM1072KJZF, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer, and low in-line power loss are needed in commercial industrial surface mount applications.

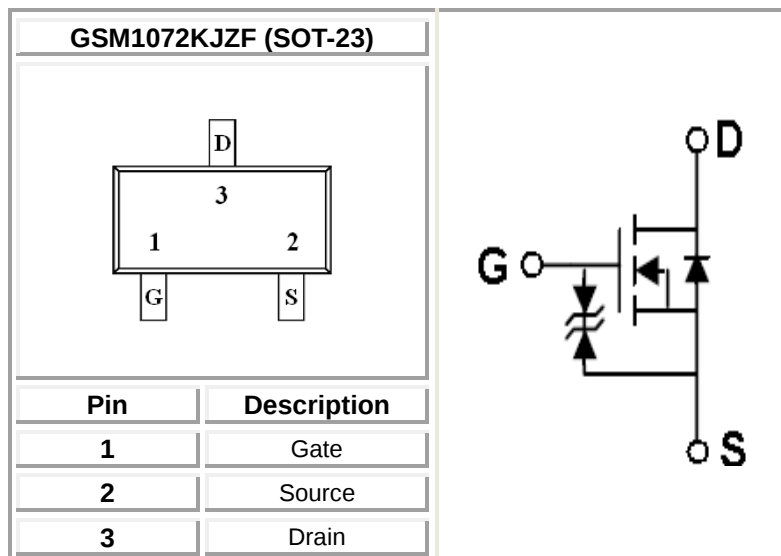
Features

- 20V/0.5A, $R_{DS(ON)}=300m\Omega@V_{GS}=4.5V$
- 20V/0.4A, $R_{DS(ON)}=450m\Omega@V_{GS}=2.5V$
- 20V/0.2A, $R_{DS(ON)}=700m\Omega@V_{GS}=1.8V$
- 20V/0.1A, $R_{DS(ON)}=1200m\Omega@V_{GS}=1.5V$
- Low Offset (Error) Voltage
- Low-Voltage Operation
- High-Speed Circuits
- Low Battery Voltage Operation
- ESD Protected
- SOT-23 package design

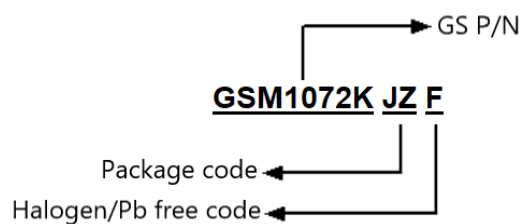
Applications

- Power Management in Notebook
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

Packages & Pin Assignments

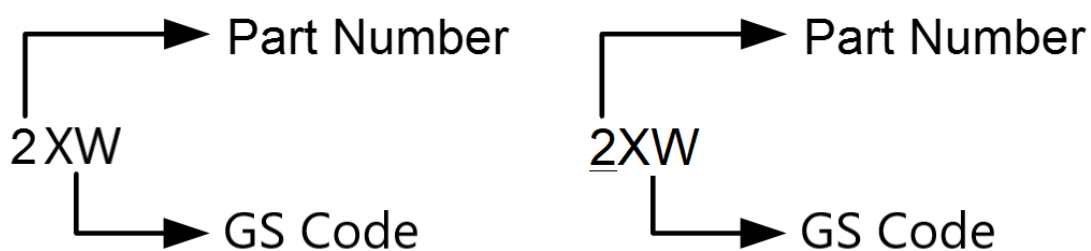


Ordering Information



Part Number	Package	Quantity Reel
GSM1072KJZF	SOT-23	3000 PCS

Marking Information



Absolute Maximum Ratings

(T_A=25°C unless otherwise noted)

Symbol	Parameter	Typical	Unit
V _{DSS}	Drain-Source Voltage	20	V
V _{GSS}	Gate-Source Voltage	±10	V
I _D	Continuous Drain Current(T _A =25°C)	0.8	A
I _{DM}	Pulsed Drain Current	3.0	A
I _S	Continuous Source Current(Diode Conduction)	0.3	A
P _D	Power Dissipation(T _A =25°C)	0.45	W
T _J	Operating Junction Temperature Range	-55 to +150	°C
T _{STG}	Storage Temperature Range	-55 to +150	°C

Electrical Characteristics

(T_A=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	20			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	0.3	0.6	1.0	
I _{GSS}	Gate Leakage Current	V _{DS} =0V, V _{GS} =±10V			10	uA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =16V, V _{GS} =0V			1	uA
		V _{DS} =16V, V _{GS} =0V T _J =85°C			30	
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =4.5V, I _D =0.5A		200	300	mΩ
		V _{GS} =2.5V, I _D =0.4A		270	450	
		V _{GS} =1.8V, I _D =0.2A		390	700	
		V _{GS} =1.5V, I _D =0.1A		570	1200	
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =0.4A		1.0		S
V _{SD}	Diode Forward Voltage	I _S =0.15A, V _{GS} =0V		0.8	1.2	V
Dynamic						
Q _g	Total Gate Charge	V _{DS} =10V, V _{GS} =4.5V, I _D ≐0.25A		0.73		nC
Q _{gs}	Gate-Source Charge			0.93		
Q _{gd}	Gate-Drain Charge			0.12		
C _{iss}	Input Capacitance	V _{DS} =16V, V _{GS} =0V f=1MHz		60.7		pF
C _{oss}	Output Capacitance			9.7		
C _{rss}	Reverse Transfer Capacitance			5.4		
t _{d(on)}	Turn-On Time	V _{DD} =10V, R _L =47Ω, I _D ≐0.2A V _{GEN} =4.5V,R _G =10Ω		5.1		ns
t _r				7.4		
t _{d(off)}	Turn-Off Time			26.7		
t _f				12.3		

Typical Performance Characteristics

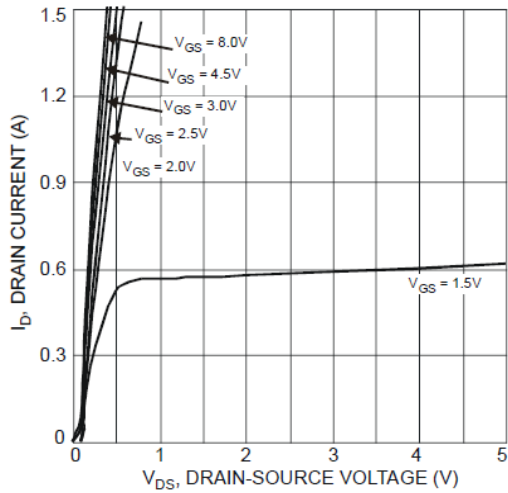


Fig. 1 Typical Output Characteristics

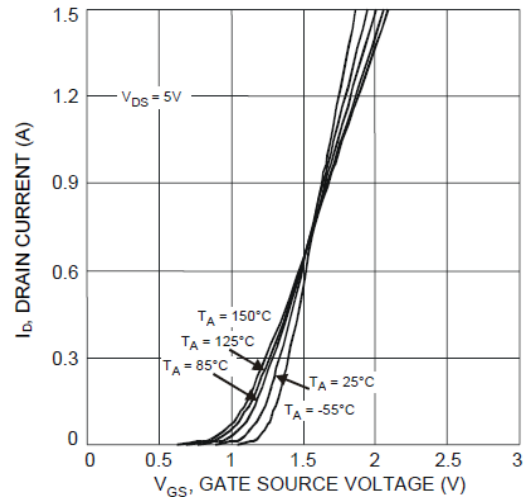


Fig. 2 Typical Transfer Characteristics

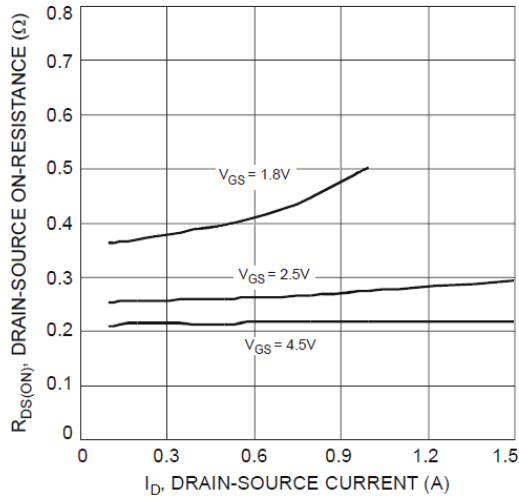


Fig. 3 Typical On-Resistance vs. I_D and V_{GS}

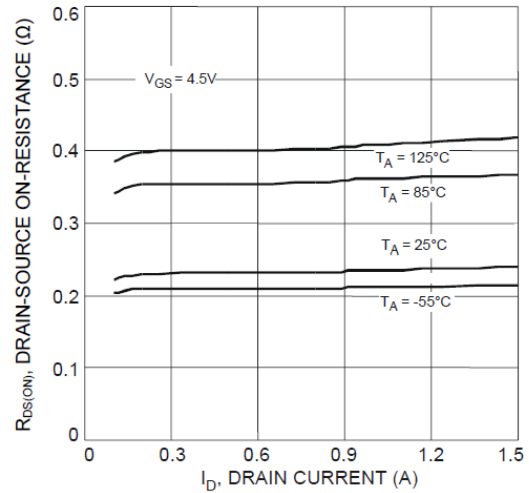


Fig. 4 Typical Drain-Source On-Resistance vs. I_D and T_J

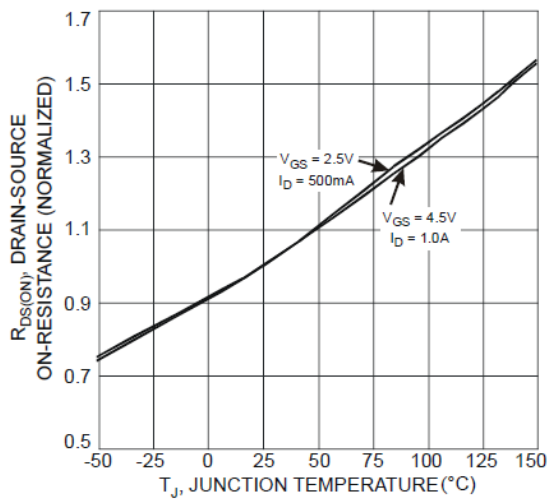


Fig. 5 On-Resistance Variation with T_J

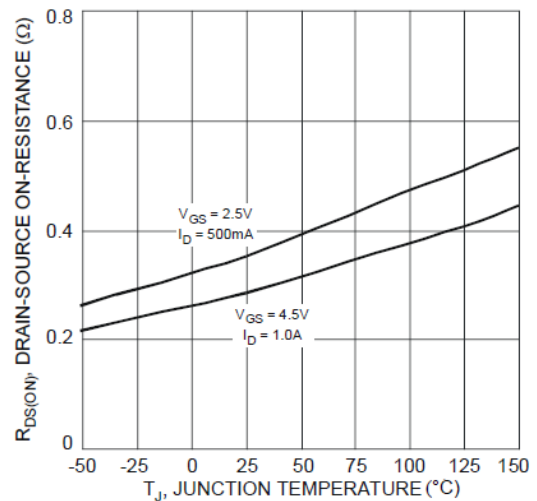


Fig. 6 On-Resistance Variation with T_J

Typical Performance Characteristics (Continue)

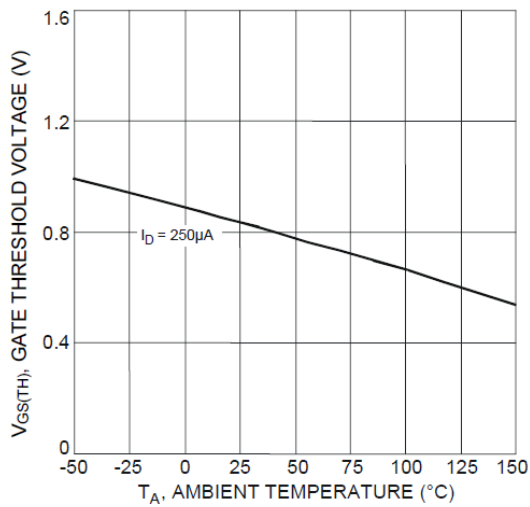


Fig. 7 Gate Threshold Variation vs. T_A

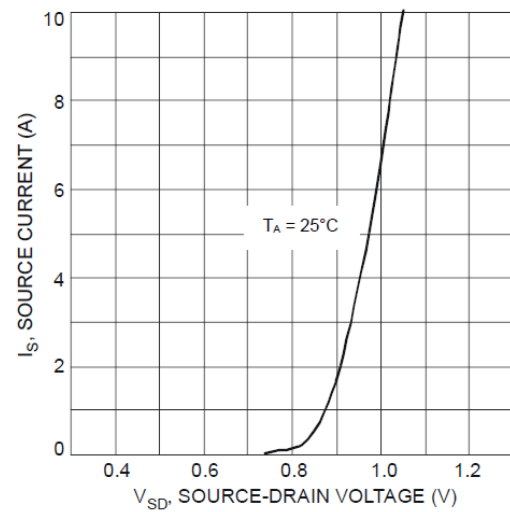


Fig. 8 Diode Forward Voltage vs. Current

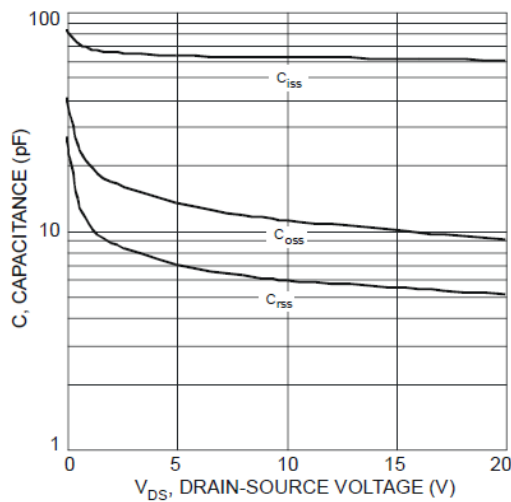


Fig. 9 Typical Capacitance

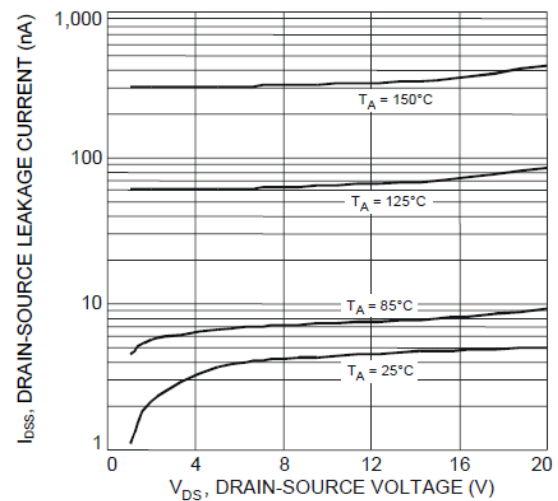


Fig. 10 Typical Drain-Source Leakage Current
vs. Drain-Source Voltage

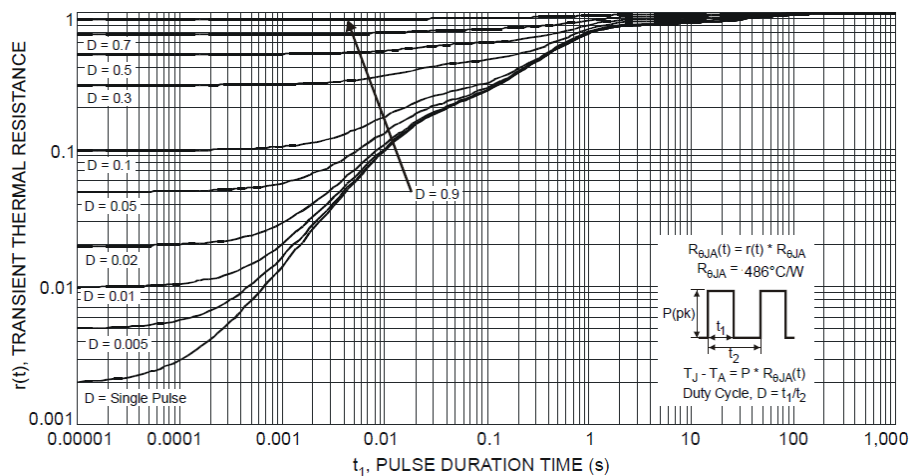
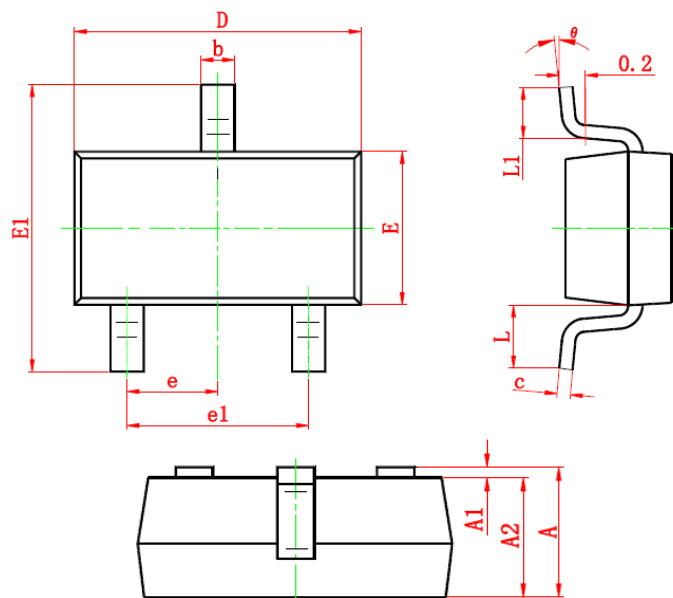


Fig. 11 Transient Thermal Response

Package Dimension

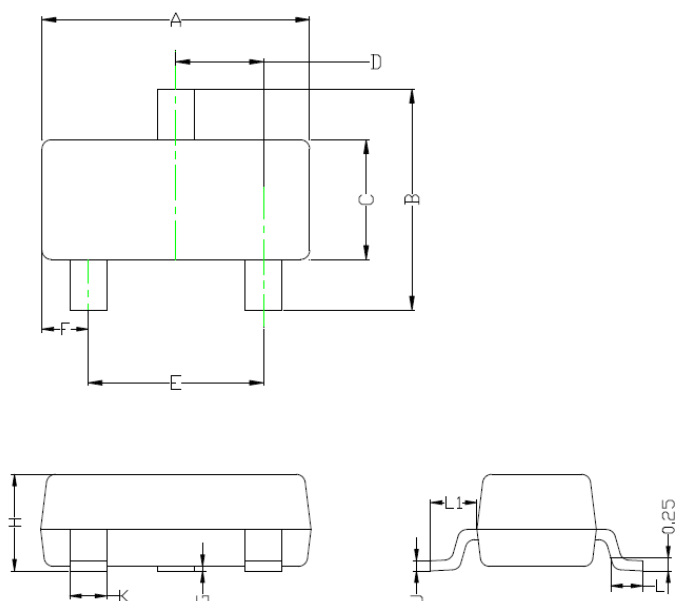
SOT-23



Dimensions

Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	0.900	1.140	0.035	0.045
A1	0.000	0.140	0.000	0.006
A2	-	1.000	-	0.039
b	0.300	0.500	0.012	0.020
c	0.070	0.130	0.003	0.005
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	6°

SOT-23



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	2.800	3.040	0.110	0.120
B	2.100	2.640	0.083	0.104
C	1.200	1.400	0.047	0.055
D	0.890	1.030	0.035	0.041
E	1.780	2.050	0.070	0.081
F	0.450	0.600	0.018	0.024
G	0.013	0.100	0.001	0.004
H	0.900	1.110	0.035	0.044
J	0.085	0.180	0.003	0.007
K	0.370	0.510	0.015	0.020
L	0.300	0.500	0.012	0.020
L1	0.500	0.600	0.020	0.024

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